EuMIC 2016 Table of Contents

EuMIC01: Si-Based Transceiver Building Blocks
Chair: Norihau Suematsu, Tohoku University
Co-Chair: Andrea Suriani, Thales Alesia
Room 10, Time 09:00–10:40, Monday 3rd October 2016

1. Reconfigurable 4 Channel Carrier Aggregation Receiver Using Harmonic Recombination Technique
    Seokwon Lee, Deachul Jeong, Hadong Jin, Bumman Kim, POSTECH, Korea

5. Integrated Circuit Field Canceller System Suitable for Highly Integrated Connectivity Transceivers
    Zaid Aboush1, Noshir Dubash1, Adem Aktas1, Luis Brions1, Jeff Koeller1,
    Rainer Herberholz2, Andrew Croxall2
    1 Qualcomm Atheros, USA; 2 Qualcomm Technologies International, UK

9. A Wideband Low Noise SiGe Medium Power Amplifier for X-Band Phased Array Applications
    Can Çalışkan1, İlker Kalyoncuı, Emre Ozeren1, Mehmet Kaynak2, Yasar Gurbuzı
    1 Sabancı University, Turkey; 2 IHP, Germany

13. Quasi-Circulator Based Automotive Monostatic Transceiver with Integrated Leakage Canceler
    Matthias Porranzl1, Christoph Wagner2, Herbert Jaeger2, Andreas Stelzer1
    1 Johannes Kepler Universität Linz, Austria; 2 DICE, Austria

EuMIC 2016 Table of Contents

EuMIC02: High Efficiency and Linear Power Amplifiers
Chair: Franco Giannini, University of Rome Tor Vergata
Co-Chair: Frank van Vliet, TNO
Room 11, Time 09:00–10:40, Monday 3rd October 2016

    I. Blednov, NXP Semiconductors, USA

    Andreas Wentzel, Maruaf Hossain, Dimitri Stoppel, Nils Weimann, Viktor Krozer,
    Wolfgang Heinrich, FBH, Germany

25. 20W S-Band High Power Amplifier Using Stacked FET Topology
    G. van der Bent, A.P. de Hek, F.E. van Vliet, TNO, The Netherlands

29. Predistortion- and Development-Platform for Multi-Input RF Power Amplifiers
    Peter Singerl1, Thomas Magesacher2, Martin Mataln1
    1 Infineon Technologies, Austria; 2 Lund University, Sweden

33. Solid-State RF Power Amplifiers for ISM CW Applications Based on 100V GaN Technology
    Gabriele Formicone1, Jeff Burger1, James Custer1, Gianni Bosi2, Antonio Raffo2,
    Giorgio Vannini2
    1 Integra Technologies, USA; 2 Università di Ferrara, Italy
### EuMIC03: Novel Characterisation Techniques for Microwave Devices

Chair: Carlos Camacho-Penalosa, Universidad de Malaga  
Co-Chair: Raymond Quéré, University of Limoges  
Room 12, Time 09:00–10:40, Monday 3rd October 2016  

<table>
<thead>
<tr>
<th>Page</th>
<th>Title</th>
<th>Authors</th>
<th>Institutions</th>
</tr>
</thead>
<tbody>
<tr>
<td>37</td>
<td>Linearity Characterization of GaN HEMT Technologies Through Innovative On-Wafer Multi-Tone Load-Pull Measurements</td>
<td>Si Abed Karim Kahil, Sylvain Laurent, Raymond Quéré, Jacques Sombrin, Didier Floriot, Valeria Brunel, Charles Teyssandier</td>
<td>XLIM, France; United Monolithic Semiconductors, France</td>
</tr>
<tr>
<td>41</td>
<td>Low-Frequency Time-Domain Characterization for Fast and Reliable Evaluation of Microwave Transistor Performance</td>
<td>Gianni Bosi, Antonio Raffo, Valeria Vadala, Francesco Trevisan, Giorgio Vannini, Omer Cengiz, Ozlem Sen, Ekrem Ozbay</td>
<td>Università di Ferrara, Italy; Bilkent University, Turkey</td>
</tr>
<tr>
<td>45</td>
<td>Short Pulse Thermal Response of HBTs</td>
<td>Kazuaki Yazawa, Dustin Kendig, Alain Xiong, Christophe Charbonniaud, Tony Gasseling, Ali Shakouri</td>
<td>Microsanj, USA; AMCAD Engineering, France; Purdue University, USA</td>
</tr>
<tr>
<td>49</td>
<td>Characterization and Modeling of Frequency Dispersion in RF LDMOS Transistors</td>
<td>Peter H. Aaen, Lei Zhang, Kevin Kim</td>
<td>University of Surrey, UK; NXP Semiconductors, USA</td>
</tr>
<tr>
<td>53</td>
<td>Characterization of a High Power GaN Device for Class E PA Design with Non-Sinusoidal Stimulus</td>
<td>Vittorio Camarchia, Elisa Cipriani, Paolo Colantonio, Marco Pirola, Roberto Quaglia, Lorenzo Cabria, Natanael Ayllon</td>
<td>Politecnico di Torino, Italy; Università di Roma “Tor Vergata”, Italy; Cardiff University, UK; TTI Norte, Spain; ESA, The Netherlands</td>
</tr>
</tbody>
</table>

### EuMIC05: GaN Devices

Chair: Frank E. van Vliet, TNO  
Co-Chair: Didier Floriot, UMS  
Room 7, Time 14:20–16:00, Monday 3rd October 2016  

<table>
<thead>
<tr>
<th>Page</th>
<th>Title</th>
<th>Authors</th>
<th>Institutions</th>
</tr>
</thead>
<tbody>
<tr>
<td>57</td>
<td>Quest for Vacuum Tubes' Replacement: 150V UHF GaN Radar Transistors</td>
<td>Gabriele Formicone, Jeff Burger, James Custer, John Walker</td>
<td>Integra Technologies, USA</td>
</tr>
<tr>
<td>61</td>
<td>Enhancement-Mode AlGaN/GaN FinFETs with High On/Off Performance in 100nm Gate Length</td>
<td>E. Ture, P. Brückner, Rüdiger Quay, Oliver Ambacher, M. Alsharef, R. Granzner, F. Schwierz</td>
<td>Fraunhofer IAF, Germany; Technische Universität Ilmenau, Germany</td>
</tr>
<tr>
<td>65</td>
<td>Normally-Off AlGaN/GaN Recessed MOS-HEMTs on Normally-On Epitaxial Structures for Microwave Power Applications</td>
<td>L. Trinh Xuan, R. Aubry, N. Michel, O. Patard, J.-C. Jacquet, S. Piotrowicz, M. Ouali, P. Gararra, C. Potier, D. Lancereau, S.L. Delage, Sylvain Laurent</td>
<td>III-V Lab, France; XLIM, France</td>
</tr>
</tbody>
</table>
EuMIC 2016 Table of Contents

EuMIC06 : Millimetre-Wave Low Noise Amplifiers
Chair: Manfred Berroth, Universität Stuttgart
Co-Chair: Didier Belot, CEA-LETI
Room 8, Time 14:20–16:00, Monday 3rd October 2016

73 A Low Power High Gain-Bandwidth E-Band LNA
Kambiz Hadipour1, Andreas Stelzer2
1DICE, Austria; 2Johannes Kepler Universität Linz, Austria

77 Cryogenic Broadband Q-Band MMIC Low-Noise Amplifier
J. Vicente Terán Collantes, Luisa de la Fuente, Beatriz Aja, Eduardo Artal, Universidad de Cantabria, Spain

81 Cryogenic Low Noise MMIC Amplifiers for U-Band (40–60GHz)
Lorena Samoska1, Andy Fung1, Pekka Kangaslahti1, Rohit Gawande1, Mary Soria1, Charles Lawrence1, Todd Gaier1, David Cuadrado-Calle2, Danielle George2, Gary Fuller2, Richard Lai3, Stephen Sarkozy3, Mikko Varonen4, Kieran Cleary5
1Jet Propulsion Laboratory, USA; 2University of Manchester, UK; 3Northrop Grumman, USA; 4Aalto University, Finland; 5Caltech, USA

EuMIC 2016 Table of Contents

EuMIC07 : Millimetre-Wave and THz Transceiver Components
Chair: Huei Wang, National Taiwan University
Co-Chair: Mehmet Kaynak, IHP
Room 9, Time 14:20–16:00, Monday 3rd October 2016

85 600GHz Resistive Mixer S-MMICs with Integrated Multiplier-by-Six in 35nm mHEMT Technology
Rainer Weber1, Axel Tessmann1, Hermann Massler1, Arnulf Leuther1, U.J. Lewark2
1Fraunhofer IAF, Germany; 2IMST, Germany

89 Balanced G-Band Gm-Boosted Frequency Doubblers in Transferred Substrate InP HBT Technology
Tom K. Johansen1, Al-Sawaf Thualfiqar2, Nils Weimann2, Wolfgang Heinrich2, Viktor Krozer2
1Technical University of Denmark, Denmark; 2FBH, Germany

93 Ku-Band to F-Band Active Multiplier Chain in 65-nm CMOS
Bassam Khamaisi, Eran Socher, Tel Aviv University, Israel

97 A 0.58–0.61THz Single On-Chip Antenna Transceiver Based on Active X30 LO Chain on 65nm CMOS
Bassam Khamaisi, Samuel Jameson, Eran Socher, Tel Aviv University, Israel

101 A 230GHz Quadrupler with 2dBm Output Power in 90nm SiGe BiCMOS Technology
Roee Ben Yishay, Danny Elad, IBM Haifa Research Lab, Israel
### EuMIC 2016 Table of Contents

#### EuMIC08: CMOS Based Transceiver Components

**Chair:** Eric Tournier, University of Toulouse - LAAS/CNRS  
**Co-Chair:** Norihau Suematsu, Tohoku University  
**Room:** 10, **Time:** 14:20–16:00, **Monday 3rd October 2016**

<table>
<thead>
<tr>
<th>Page</th>
<th>Title</th>
<th>Authors</th>
</tr>
</thead>
<tbody>
<tr>
<td>105</td>
<td>Optical Receiver Amplifier with Adaptive Power and Bandwidth for up to 30Gbit/s in 28nm CMOS</td>
<td>Laszlo Szilagyi, David Schoeniger, Ronny Henker, Frank Ellinger, Technische Universität Dresden, Germany</td>
</tr>
</tbody>
</table>
| 109  | An Integrated Dual-Band Transmitter for Vital Sign Detection Radar Applications in 0.18-μm CMOS | Jen-Hao Cheng¹, Yi-Hsien Lin¹, Wen-Jie Lin¹, Jeng-Han Tsai², Tian-Wei Huang¹, Huei Wang¹  
  ¹National Taiwan University, Taiwan; ²National Taiwan Normal University, Taiwan |
| 113  | Non-Invasive Highly Integrated Transformer Power Detector for Self-Healing PA in 130nm H9SOI-FEM CMOS Technology | Boris Moret¹, Eric Kerhervé¹, Vincent Knopik²  
  ¹IMS (UMR 5218), France; ²STMicroelectronics, France |
| 117  | A 4-Bit Broadband CMOS Phase Shifter Using Magnetically Coupled All-Pass Networks | Jun-Jie Huang, Hsiao-Yun Li, Jia-Shiang Fu, National Central University, Taiwan |
| 121  | MOSFET Divide-by-Four Frequency Divider with Injection Locking at Main-Gate and Back-Gate | Janne-Wha Wu, Chih-Ho Tu, Sheng-Wen Chen, Lo-Chun Tung, National Chung Cheng University, Taiwan |

### EuMIC 2016 Table of Contents

#### EuMIC09: Doherty and Envelope Tracking Amplifier Solutions

**Chair:** Paolo Colantonio, University of Rome Tor Vergata  
**Co-Chair:** Marc van Heijningen, TNO  
**Room:** 11, **Time:** 14:20–16:00, **Monday 3rd October 2016**

<table>
<thead>
<tr>
<th>Page</th>
<th>Title</th>
<th>Authors</th>
</tr>
</thead>
</table>
| 125  | All Gallium Nitride Envelope-Tracking Multiband Power Amplifier Using 200MHz Switching Buck-Converter | Takanoob Fujiwara¹, Kenji Mukai¹, Hideyuki Nakamizo¹, Shintaro Shinjo¹, Jonmei J. Yan², Hamed Gheidi², Peter Asbeck³  
  ¹Mitsubishi Electric, Japan; ²MaXentric Technologies, USA; ³University of California at San Diego, USA |
| 129  | Optimized Peaking Amplifier of Doherty Amplifier Using an Inductive Input Second Harmonic Load | Seokhyeon Kim, Juyeon Lee, Kyunghoon Moon, Yunsik Park, Donggyu Minn, Bumman Kim, POSTECH, Korea |
| 133  | A Design Approach to Mitigate the Phase Distortion in GaN MMIC Doherty Power Amplifiers | Rocco Giofré, Paolo Colantonio, Franco Giannini, Università di Roma "Tor Vergata", Italy |
| 137  | Novel Output Combiner for Three-Way Doherty Power Amplifiers | R. Lehna, A. Bangert, Universität Kassel, Germany |
| 141  | Optimization of Idle Current in Envelope Tracking Power Amplifier for Efficiency and Linearity | Kyunghoon Moon, Yunsung Cho, Jooseung Kim, Byungjoon Park, Hadong Jin, Junho Shin, Bumman Kim, POSTECH, Korea |
EuMIC 2016 Table of Contents

EuMIC10: Modelling of Thermal and Trapping Effects in HEMTs
Chair: Thomas Brazil, University College Dublin
Co-Chair: Christopher Duff, The University of Manchester
Room 12, Time 14:20–16:00, Monday 3rd October 2016

145 Thermal Analysis of AlN/GaN/AlGaN HEMTs Grown on Si and SiC Substrate Through TCAD Simulations and Measurements
A.K. Sahoo1, N.K. Subramani1, J.-C. Nallatamby1, R. Sommet1, Raymond Quéré1, N. Rolland2, F. Medjdoub2
1XLIM, France; 2IEMN, France

149 Anomaly and Intrinsic Capacitance Behaviour Over Temperature of AlGaN/GaN/SiC and AlGaAs/GaAs HEMTs for Microwave Application
Mohammad A. Alim1, Ali A. Rezazadeh1, Norshakila Haris1, Christophe Gaquiere2
1University of Manchester, UK; 2IEMN, France

153 Characterization and Modeling of Traps and RF Frequency Dispersion in AlGaN/AIN/GaN HEMTs
Héctor Sánchez-Martín1, Óscar García-Pérez1, Ignacio Iñiguez-de-la-Torre1, Susana Pérez1, Tomás González1, Javier Mateos1, Philippe Almanta2, Nicolas Deffrance2, Marie Lesecq2, Virginie Hoel2, Yvon Cordier3, Stéphanie Rennesson3
1Universidad de Salamanca, Spain; 2IEMN, France; 3CHREA, France

157 Novel Approach to Trapping Effect Modeling Based on Chalmers Model and Pulsed S-Parameter Measurements
Peng Luo, Olof Bengtsson, Matthias Rudolph, FBH, Germany

161 Characterization of Trapping in a GaN HEMT by Performing Isothermal Three-Stage Pulse Measurements
Sayed Ali Albahrani1, Anthony E. Parker1, Graham Town1, Michael C. Heimlich1, Bryan K. Schwitter2, Simon J. Mahon2
1Macquarie University, Australia; 2M/A-COM Technology Solutions, Australia

EuMIC 2016 Table of Contents

EuMIC11: Graphene & III-V Devices
Chair: Giovanni Ghione, Politecnico di Torino, DET
Co-Chair: Ingmar Kallfass, University of Stuttgart
Room 7, Time 16:40–18:20, Monday 3rd October 2016

165 Graphene Field Effect Transistors on Flexible Substrate: Stable Process and High RF Performance
W. Wei1, E. Pallecchi1, M. Belhaj1, A. Centeno2, Z. Amalà2, D. Vignaud1, H. Happy1
1IEMN, France; 2Graphenea, Spain

169 Monolithic Integration of Vertical-Oriented Schottky Diode Using 0.5×200μm2 GaAs pHEMT for Limiter Applications
Norshakila Haris1, Peter B.K. Kyabaggu2, Mohammad A. Alim1, Ali A. Rezazadeh1
1University of Manchester, UK; 2Bukoola General Enterprises, Uganda

173 High-Performance Self-Aligned InAs MOSFETs with L-Shaped Ni-Epilayer Alloyed Source/Drain Contact for Future Low-Power RF Applications
Mohamed Ridaaou1, Alain-Bruno Fadgie-Djomkam1, Matej Pastorek1, Nicolas Wichmann1, Abdelatif Jauad2, Hassan Maher2, Sylvain Bollaert1
1IEMN, France; 2Université de Sherbrooke, Canada

N/A Frequency Limitations of the Nitride and Arsenide HEMTs
Yu.V. Fedorov, S.V. Mikhailovich, Russian Academy of Sciences, Russia
### EuMIC 2016 Table of Contents

#### EuMIC12: Millimetre-Wave Transceiver Components

**Chair:** Roee Ben Yishay, IBM Haifa Research Lab  
**Co-Chair:** Herbert Zirath, Chalmers University  
**Room 8, Time 16:40–18:20, Monday 3rd October 2016**

1. **A Wideband Fully Integrated SiGe Chipset for High Data Rate Communication at 240GHz**  
   N. Sarmah\(^1\), P.R. Vazquez\(^1\), J. Grzyb\(^1\), W. Foerster\(^1\), Bernd Heinemann\(^2\), Ullrich R. Pfeiffer\(^1\)  
   \(^1\)Bergische Universität Wuppertal, Germany; \(^2\)IHP, Germany

2. **A 275GHz Amplifier in 0.13μm SiGe**  
   Stefan Malz\(^1\), Philipp Hillger\(^1\), Bernd Heinemann\(^2\), Ullrich R. Pfeiffer\(^1\)  
   \(^1\)Bergische Universität Wuppertal, Germany; \(^2\)IHP, Germany

3. **A 280GHz Stacked-FET Power Amplifier Cell Using 50nm Metamorphic HEMT Technology**  
   B. Amado-Rey\(^1\), Y. Campos-Roca\(^2\), C. Friesicke\(^1\), Axel Tessmann\(^1\), R. Lozar\(^1\), S. Wagner\(^1\), Arnulf Leuther\(^1\), Michael Schlechtweg\(^1\), Oliver Ambacher\(^1\)  
   \(^1\)Fraunhofer IAF, Germany; \(^2\)Universidad de Extremadura, Spain

4. **A 300-GHz 64-QAM CMOS Transmitter with 21-Gb/s Maximum Per-Channel Data Rate**  
   Kyoya Takano, Kosuke Katayama, Shuhei Amakawa, Takeshi Yoshida, Minoru Fujishima, Hiroshima University, Japan

---

#### EuMIC 2016 Table of Contents

#### EuMIC13: VCOs and Synthesizers

**Chair:** Georg Böck, TU Berlin  
**Co-Chair:** Eric Tournier, University of Toulouse - LAAS/CNRS  
**Room 10, Time 16:40–18:20, Monday 3rd October 2016**

1. **A 2-GHz-Band Low-Phase-Noise VCO IC with an LC Bias Circuit in 180-nm CMOS**  
   Xiao Xu, Xin Yang, Toshihiko Yoshimasu, Waseda University, Japan

2. **A Ka-Band BiCMOS LC-VCO with Wide Tuning Range and Low Phase Noise Using Switched Coupled Inductors**  
   Maciej Kucharski, Frank Herzel, Herman Jalli Ng, Dietmar Kissinger, IHP, Germany

3. **Wideband High-Linearity Low-Phase-Noise VCO for Space Communication Systems**  
   L. Pantoli\(^1\), L.N. Di Muccio\(^1\), G. Leuzzi\(^1\), A. Barigelli\(^2\), F. Vitulli\(^2\)  
   \(^1\)Università dell’Aquila, Italy; \(^2\)Thales Alenia Space, Italy

4. **A 17.5–22.5GHz Fractional-N Wideband Frequency Synthesizer in 65nm CMOS Technology**  
   K. Giannakidis\(^1\), S. Sgourenas\(^1\), A. Kanteres\(^1\), G. Kalivas\(^1\), K. Moustakas\(^2\), S. Siskos\(^2\)  
   \(^1\)University of Patras, Greece; \(^2\)Aristotle University of Thessaloniki, Greece

5. **A -194.0dBc/Hz FoM CMOS Tail-Filtering VCO Using Helium-3 Ion Irradiation Technique**  
   Hanli Liu\(^1\), Ning Li\(^1\), Aravind Tharayil Narayanan\(^1\), Teerachot Siriburanon\(^1\), Takanori Hirano\(^1\), Kenichi Okada\(^1\), Akira Matsuzawa\(^1\), Takeshi Inoue\(^2\), Hitoshi Sakane\(^2\)  
   \(^1\)Tokyo Institute of Technology, Japan; \(^2\)SHIEI, Japan
EuMIC 2016 Table of Contents

EuMIC14 : GaN Power Amplifiers
Chair: Frank van den Bogaart, TNO
Co-Chair: Ernesto Limiti, University of Rome Tor Vergata
Room 11, Time 16:40–18:20, Monday 3rd October 2016

217   A 1–8GHz Gallium Nitride Distributed Power Amplifier MMIC Utilizing a Trifilar Transformer
Charles F. Campbell, Michael D. Roberg, Jonathan Fain, Sabyasachi Nayak, Qorvo, USA

221   Stability Analysis and Demonstration of an X-Band GaN Power Amplifier MMIC
M. van Heijningen\textsuperscript{1}, A.P. de Hek\textsuperscript{1}, F.E. van Vliet\textsuperscript{1}, S. Dellier\textsuperscript{2}
\textsuperscript{1}TNO, The Netherlands; \textsuperscript{2}AMCAD Engineering, France

225   A Miniature 70W Quasi-MMIC PA Block Suitable for Highly Integrated X-Band Pulsed SSPA Schemes
Davide Resca, Francesco Scappaviva, MEC, Italy

229   Broadband 2-Stage GaN Power Amplifier in an 8×8mm Package
Shingo Inoue, Kaname Ebihara, Sumitomo Electric Device Innovations, Japan

233   Internally-Packaged-Matched Continuous Inverse Class-FI Wideband GaN HPA
V. Carrubba\textsuperscript{1}, S. Maroldt\textsuperscript{2}, E. Ture\textsuperscript{2}, U. Udeh\textsuperscript{2}, M. Mußer\textsuperscript{2}, W. Bronner\textsuperscript{2}, Rüdiger Quay\textsuperscript{2}, Oliver Ambacher\textsuperscript{2}
\textsuperscript{1}Ericsson, Sweden; \textsuperscript{2}Fraunhofer IAF, Germany

EuMIC 2016 Table of Contents

EuMIC15 : Device Modelling of Microwave FETs
Chair: Teresa M. Martin-Guerrero, Universidad de Malaga
Co-Chair: Jean-Christophe Nallatamby, University of Limoges
Room 12, Time 16:40–18:20, Monday 3rd October 2016

237   Physics-Based Modeling of FinFET RF Variability
A.M. Bugn, S. Donati Guerrieri, F. Bonani, G. Ghione, Politecnico di Torino, Italy

241   Dual-Gate HEMT Parameter Extraction Based on 2.3D Multiport Simulation of Passive Structures
Friedbert van Raay, Rüdiger Quay, D. Schwantuschke, Matthias Ohlrogge, Detlef Peschel, Michael Schlechtweg, Oliver Ambacher, Fraunhofer IAF, Germany

245   On the Modeling of High Power FET Transistors
Ilcho Angelov, Mattias Thorsell, Marcus Gavel, Oliver Barrera, Chalmers University of Technology, Sweden

249   Development and Verification of a Scalable GaAs pHEMT FEM Thermal Model
Bryan K. Schwitter\textsuperscript{1}, Anthony P. Fattorini\textsuperscript{1}, Simon J. Mahon\textsuperscript{1}, Anthony E. Parker\textsuperscript{2}, Michael C. Heimlich\textsuperscript{2}
\textsuperscript{1}M/A-COM Technology Solutions, Australia; \textsuperscript{2}Macquarie University, Australia

253   An EM-Based Approach to Model a Gallium Nitride HEMT in a Custom Common-Gate Configuration
Rocco Giofré, Sergio Colangeli, Walter Ciccognani, Ernesto Limiti, Università di Roma “Tor Vergata”, Italy
EuMIC 2016 Table of Contents

EuMIC16: CMOS and BiCMOS Power Amplifiers
Chair: Eric Kerherve, IMS Bordeaux
Co-Chair: Patrick Schuh, Airbus EDS
Room 14, Time 09:00–10:40, Tuesday 4th October 2016

257  A SiGe-Based Broadband 100–180GHz Differential Power Amplifier with 11dBm Peak Output Power and >1.3THz GBW
Faisal Ahmed¹, Muhammad Furqan¹, Klaus Aufinger², Andreas Stelzer¹
¹Johannes Kepler Universität Linz, Austria; ²Infineon Technologies, Germany

261  14dBm, 18–20GHz Injection-Locked Power Amplifier with 45% Peak PAE in 65nm CMOS
Ahmed Hamed, Mohamed Saeed, Renato Negra, RWTH Aachen University, Germany

265  15GHz 25dBm Multigate-Cell Stacked CMOS Power Amplifier with 32% PAE and ≥30dB Gain for 5G Applications
Narek Rostomyan, Jefy A. Jayamon, Peter Asbeck, University of California at San Diego, USA

269  3.4 to 4.8GHz 65nm CMOS Power Amplifier for Ultra Wideband Location Tracking Application in Emergency and Disaster Situations
David Polge¹, Anthony Ghiotto¹, Eric Kerhervé², Pascal Fabre²
¹IMS (UMR 5218), France; ²BeSpoon, France

273  Highly Linear Wideband CMOS RF Power Amplifier with Active Feedback in 130nm CMOS Technology
Muhammad Abdullah Khan, Pierre Bousseaud, Renato Negra, RWTH Aachen University, Germany

EuMIC 2016 Table of Contents

EuMIC17: Novel Modelling Techniques for Microwave Circuit Design
Chair: Rob Sloan, University of Manchester
Co-Chair: Edouard Ngoya, University of Limoges
Room 15, Time 09:00–10:40, Tuesday 4th October 2016

277  Prediction of Odd-Mode Instabilities Under Output Mismatch Effects
Franco Ramírez, Almudena Suárez, Sergio Sancho, Universidad de Cantabria, Spain

281  Broadband Non-Linear FET Behavioral Model Defined in the Admittance Domain
M. Rocio Moure¹, Monica Fernandez-Barciela¹, Michael Casbon², Paul J. Tasker²
¹Universidad de Vigo, Spain; ²Cardiff University, UK

285  Fast Extraction of Accurate I/V Models for Harmonically-Tuned Power Amplifier Design
Valeria Vadalà¹, Antonio Raffo¹, Gianni Bosi¹, Giorgio Vannini¹, Paolo Colantonio², Franco Giannini²
¹Università di Ferrara, Italy; ²Università di Roma “Tor Vergata”, Italy

289  EM Analysis of Ka Band Multi-Throw PIN Diode MMIC Switches
Andrzej Rozbicki, James J. Brogle, M/A-COM Technology Solutions, USA

293  Inverse Surrogate Models for Fast Geometry Scaling of Miniaturized Dual-Band Couplers
Slawomir Koziel, Adrian Bekasiewicz, Reykjavik University, Iceland
EuMIC 2016 Table of Contents

EuMIC18: High Power and T/R Modules — GaN Based Components
Chair: Massimo C. Comparini, Telespazio
Co-Chair: Georg Böck, TU Berlin
Room 17, Time 09:00–10:40, Tuesday 4th October 2016

297  Compact GaN MMIC T/R Module Front-End for X-Band Pulsed Radar
Andrea Biondi, Sara D’Angelo, Francesco Scappaviva, Davide Resca, Vito Antonio Monaco, MEC, Italy

301  Overview of the MAGNUS Project
Philippe Duême¹, Benoît Mallet-Guy¹, Yves Mancuso⁴, Niklas Billström², Clément Tolant³, Hervé Brouzes⁴, Patrick Schuh⁷, David Hone⁶, Rashid Fazaldin⁷
¹Thales Systèmes Aéropostés, France; ²Saab, Sweden; ³Thales Air Systems, France;
⁴Thales Nederland, The Netherlands; ⁵Airbus Defence & Space, Germany; ⁶Selex ES, UK;
⁷Thales UK, UK

305  A Q-Band Power Amplifier MMIC Using 100nm AlGaN/GaN HEMT
Philip Feuerschütz¹, C. Friesicke², Rüdiger Quay², Arne F. Jacob¹
¹Technische Universität Hamburg-Harburg, Germany; ²Fraunhofer IAF, Germany

309  Dependence of a Hybrid 125W S-Band Switch-Limiter Receiver Protector’s Performance on Packaging Technique — Plastic/Leadframe QFN vs. Ceramic/Air-Cavity SMT
James J. Brogle, Joseph G. Bukowski, Timothy Boles, M/A-COM Technology Solutions, USA

EuMIC 2016 Table of Contents

EuMIC19: Millimetre-Wave Signal Generation
Chair: Michael Schlechtweg, Fraunhofer IAF
Co-Chair: Shmuel Auster, Elta Systems Ltd.
Room 8–11, Time 14:20–16:00, Tuesday 4th October 2016

Jidan Al-Eryani¹, Herbert Knapp², Hao Li², Jonas Wursthorn¹, Klaus Aufinger², Soran Majied², Sabine Boguth², Rudolf Lachner², Josef Böck², Linus Maurer¹
¹Universität der Bundeswehr München, Germany; ²Infineon Technologies, Germany

317  Design of Voltage Controlled Oscillators (VCOs) in D-Band and their Phase Noise Measurements Using Frequency Down-Conversion
U. Ali, M. Bober, A. Thiede, Universität Paderborn, Germany

321  Millimeter-Wave Linear Fast-Chirp Pulse Generator in 65-nm CMOS Technology
Hiroshi Matsumura, Yohei Yajishita, Ikuo Soga, Yoichi Kawano, Taisuke Iwai, Fujitsu Laboratories, Japan

325  A 61GHz Frequency Synthesizer in SiGe BiCMOS for 122GHz FMCW Radar
Arzu Ergintav¹, Yaoming Sun², Frank Herzel¹, Herman Jalli Ng¹, Gunter Fischer¹, Dietmar Kissinger¹
¹IHP, Germany; ²HK Microsystem Integration, China

329  Transceiver MMIC’s for Street Surveillance Radar
Integrated Microfluidic Channel with Wire-Bonded Structure Solenoid for Tuneable Inductor Application

Multi-Objective Optimization of Microwave Couplers Using Corrected Domain Patching
Slawomir Koziel, Adrian Bekasiewicz, Reykjavik University, Iceland

Effects of Buffer Leakage Current on Breakdown Voltage in AlGaN/GaN HEMTs with a High-k Passivation Layer
Yoshiki Satoh, Hideyuki Hanawa, Kazushige Horio, Shibaura Institute of Technology, Japan

Nonlinear GaAs pHEMT Model with Trapping Effect for Small Signal and Dynamic Large Signal Design
A. Olomo, Infineon Technologies, Austria

A Surface Potential Large Signal Model for AlGaN/GaN HEMTs
Qingzhi Wu¹, Yuehang Xu¹, Zhang Wen¹, Yan Wang², Ruimin Xu¹
¹UESTC, China; ²Tsinghua University, China

Characterization and Modelling of 40nm mHEMT Process up to 110GHz
R. Cleriti¹, Walter Ciccognani¹, Sergio Colangeli¹, Ernesto Limiti¹, P. Frijlink², M. Renvoisé²
¹Università di Roma “Tor Vergata”, Italy; ²OMMIC, France

Load-Pull Circles Analysis Method for Applying the Outphasing Technique in Power Amplifier Design
Yolanda Jato¹, Amparo Herrera¹, Francis C. Huin²
¹Universidad de Cantabria, Spain; ²ACCO Semiconductors, France

Common-Denominator Modelling for Stability Analysis of Electronic Circuits
Adam Cooman¹, Francesco Ferranti¹, Yves Rolain¹, Gerd Vandersteen¹, Ebrahim Louarroudi²
¹Vrije Universiteit Brussel, Belgium; ²Universiteit Antwerpen, Belgium

Accurate FEM Base nMOS Switch Modelling Technique for RF Applications
Fadoua Gacim¹, Philippe Descamps², Nathalie Jourdan¹
¹NXP Semiconductors, France; ²LaMIPS, France

Controlling the Characteristics of Nanomechanical Resonators
Anastasiia Y. Nimets¹, Klaus Schuenemann¹, Dmytro M. Vavriv²
¹Technische Universität Hamburg-Harburg, Germany; ²NASU, Ukraine

A Low-Cost 180nm BiCMOS Technology with Horizontal Current Bipolar Transistor (HCBT) for Wireless Communication ICs
Josip Žilak¹, Marko Korčić¹, Tomislav Sulgaj¹, Hidenori Mochizuki², So-ichi Morita²
¹University of Zagreb, Croatia; ²Asahi Kasei Microdevices, Japan

A K-Band High-Gain Down-Converter Mixer Using Cross Couple Pair Active Load
Yu-Teng Chang, Hsin-Yu Wu, Hsin-Chia Lu, National Taiwan University, Taiwan

A 6–46GHz, High Output Power Distributed Frequency Doubler Using Stacked FETs in 0.25μm GaAs pHEMT
Thuy Nguyen¹, Duy P. Nguyen¹, Kohei Fujii², Anh-Yu Pham¹
¹University of California at Davis, USA; ²M/A-COM Technology Solutions, USA
<table>
<thead>
<tr>
<th>Page</th>
<th>Title</th>
<th>Authors</th>
</tr>
</thead>
<tbody>
<tr>
<td>389</td>
<td>0.61THz Radiating Source with On-Chip Antenna on 65nm CMOS</td>
<td>Bassam Khamaisi, Samuel Jameson, Eran Socher, Tel Aviv University, Israel</td>
</tr>
<tr>
<td>393</td>
<td>A 154–165GHz LNA and Receiver in CMOS 65nm Technology</td>
<td>Jenia Elkind, Eran Socher, Tel Aviv University, Israel</td>
</tr>
<tr>
<td>397</td>
<td>A 49-to-64GHz Frequency Doubler Using Active CS-Based Gm-Boosted Technique in 90nm CMOS Process</td>
<td>Guan-Yu Chen, Hong-Yeh Chang, Yu-Cheng Liu, Shou-Hsien Weng, Yue-Ming Hsin, National Central University, Taiwan</td>
</tr>
<tr>
<td>401</td>
<td>Miniature Fully-Integrated 2.5 and 3.5GHz LDMOS Power Amplifiers in 40-nm CMOS Technology</td>
<td>Ming-Hang Wu¹, Tien-Tzu Chang¹, Jen-Hao Cheng¹, Tian-Wei Huang¹, Jeng-Han Tsai² ¹National Taiwan University, Taiwan;²National Taiwan Normal University, Taiwan</td>
</tr>
<tr>
<td>405</td>
<td>NARMA Based Novel Closed Loop Digital Predistortion Using Moore-Penrose Inverse Technique</td>
<td>Deepak Nair M.V., Rocco Giofre', Paolo Colantonio, Franco Giannini, Università di Roma “Tor Vergata”, Italy</td>
</tr>
<tr>
<td>409</td>
<td>A 21dBm 60GHz SiGe Power Amplifier Using Modified Wilkinson Combiner</td>
<td>Roei Ben Yishay, Danny Elad, IBM Haifa Research Lab, Israel</td>
</tr>
<tr>
<td>413</td>
<td>Highly Linear Fully Integrated Class-O Power Amplifier in Standard 65nm CMOS Technology</td>
<td>Muh-Dey Wei, Renato Negra, RWTH Aachen University, Germany</td>
</tr>
<tr>
<td>417</td>
<td>Submillimetre Rectangular Waveguides Based on SU-8 Photoresist Micromachining Technology</td>
<td>David Glynn, Tianhao He, Jeff Powell, Yingtao Tian, Xiaobang Shang, Michael J. Lancaster, University of Birmingham, UK</td>
</tr>
<tr>
<td>421</td>
<td>Challenges of Wearable Antenna Design</td>
<td>Sema Dumanli, Toshiba Research Europe, UK</td>
</tr>
<tr>
<td>424</td>
<td>Broadband Push-Pull Power Amplifier Design at Microwave Frequencies</td>
<td>R.M.H. Smith¹, S.C. Cripps² ¹Plextek RFI, UK;²Cardiff University, UK</td>
</tr>
<tr>
<td>428</td>
<td>Understanding the 3 Level Doherty</td>
<td>Michael James Roberts, Slipstream Engineering Design, UK</td>
</tr>
<tr>
<td>433</td>
<td>Beyond RF Ablation: Other Uses for RF Within the Body</td>
<td>Olive Murphy¹, Mohammad Reza Bahnanyar², Christopher N. McLeod², Christofer Toumazou³, Majdi Yacoub¹ ¹Analog Devices, Ireland;²Imperial College London, UK;³Harefield Hospital, UK</td>
</tr>
</tbody>
</table>
EuMIC/EuMC02: RF MEMS Components and Packaging
Chair: Stepan Lucyszyn, Imperial College London
Co-Chair: Kamal K Samanta, AMWT Ltd
Room 13, Time 09:00–10:40, Tuesday 4th October 2016

436 High-Q Tunable Filter with a Novel Tuning Structure
J. Jiang, Raafat R. Mansour, University of Waterloo, Canada

440 Advances in MEMS Switches for RF Test Applications
Tamir Moran¹, Chris Keimel², Todd Miller³
¹National Instruments, USA; ²Menlo Microsystems, USA; ³GE Global Research, USA

444 Development of a DC to K-Band Ultra Long On-Life RF MEMS Switch with Integrated
Driver Circuitry
Eric Carty, Padraig Fitzgerald, Padraig McDaid, Bernard Stenson, Raymond Goggin,
Analogue Devices, Ireland

448 High Q Zero Level Packaged RF-MEMS Switched Capacitor Arrays
Kévin Nadaud¹, Fabien Roubeau¹, Arnaud Pothier¹, Pierre Blondy¹, Lin-Yang Zhang²,
Romain Stefanini²
¹XLIM, France; ²AirMems, France

452 Thin Film Wafer Level Encapsulated RF-MEMS Switch for D-Band Applications
S. Tolunay Wipf, A. Görüt, M. Wietstruck, C. Wipf, B. Tillack, Andreas Mai,
Mehmet Kaynak, IHP, Germany

EuMIC/EuMC03: THz Photonics Electronic Components and Systems
Chair: Mohamed Elkhouly, Robert Bosch
Co-Chair: Antti Räisänen, Aalto University
Room 1, Time 14:20–16:00, Tuesday 4th October 2016

456 Photonic BiCMOS Technology — Enabler for Si-Based, Monolithically Integrated
Transceivers Towards 400 Gbps
Stefan Lischke, Dieter Knoll, Lars Zimmermann, Pedro Rito, Ahmet Cagri Ulusoy,
Ahmet Awny, Despoira Petouli, Iria Garcia Lopez, Christian Mai, Marcel Kroh,
Bernd Heinemann, Holger Rücker, Rainer Barth, Jens Katzer, Markus Andreas Schubert,
Mehmet Kaynak, Andreas Mai, IHP, Germany

460 GaN Laser Driver Switching 30A in the Sub-Nanosecond Range
Armin Liero, Andreas Klehr, Thomas Hoffmann, Thomas Prziwara, Wolfgang Heinrich,
FBH, Germany

464 Electronic Stabilization Methods for a Single-Loop Opto-Electronic Oscillator
Mehmet Alp Ilgaz, Luka Bogataj, Boštjan Batašelj, Matjaž Vidmar, University of Ljubljana,
Slovenia

468 High-Conversion-Gain 100-GHz Photoreceiver Integrated with UTC-PD and PHEMT
Amplifier for 92-GHz Carrier, 10.7-Gbps Photonic Wireless Communication
T. Umezawa¹, K. Kashima², A. Kanno¹, P.T. Dat³, K. Akahane¹, A. Matsumoto¹,
N. Yamamoto¹, T. Kawanishi¹
¹NICT, Japan; ²Hitachi Kokusai Electric, Japan

472 Characterization of Sub-THz Detection Array in 0.18μm CMOS Technology
Jixin Chen, Weitian Liu, Pinpin Yan, Chenwei Jia, Debing Hou, Chao Yu, Wei Hong,
Southeast University, China
**EuMIC/EuMC04 : Components for Receivers**

**Chair:** Philippe Descamps, University of Caen  
**Co-Chair:** Jan Grahn, Chalmers University of Technology  
**Room 4, Time 14:20–16:00, Tuesday 4th October 2016**

476  
**Geodetic VLBI Ultra Low Noise Broad-Band Receiver for 13 Meter VGOS Radiotelescopes**  
Pablo García-Carrenõ1, Sonia García-Álvaro1, José A. López-Pérez1, María Patino-Esteban1, José M. Serna1, Beatriz Vaquero-Jiménez1, José A. López-Fernández1, Pablo-Luis López-Espi2, Rocio Sánchez-Montero2  
1Instituto Geográfico Nacional, Spain; 2Universidad de Alcalá, Spain

480  
**Self-Biasing Effects Induced by RF Step-Stress in Ka-Band LNAs Based on InAlN/GaN HEMT Technology**  
J.G. Tartarin1, S.D. Nsele1, S. Piotrowicz2, S.L. Delage2  
1LAAS, France; 2III-V Lab, France

484  
**A 30–50GHz Reflection-Type Phase Shifter Based on Slow-Wave Coupled Lines in BiCMOS 55nm Technology**  
Zyad Iskandar1, Jose Lugo-Alvarez1, Alfredo Bautista1, Emmanuel Pistono1, Florence Podevin1, Vincent Puyal2, Alexandre Siligaris2, Philippe Ferrari1  
1IMEP-LAHC, France; 2CEA-LETI, France

488  
**A High Image Rejection E-Band Sub-Harmonic IQ Demodulator with Low Power Consumption in 90-nm CMOS Process**  
Yu-Ting Chou, Yu-Hsuan Lin, Huei Wang, National Taiwan University, Taiwan

**EuMIC/EuMC05 : Multi-Functional Tuneable Filters for Wireless Applications**

**Chair:** Mehmet Karaaslan, e2v Technologies  
**Co-Chair:** Jose L. Alonso, Technical University of Madrid  
**Room 13, Time 14:20–16:00, Tuesday 4th October 2016**

492  
**A Band-Switchable and Tunable Nested Bandpass Filter With Continuous 0.4–3GHz Coverage**  
Keiichi Motoi, Naoki Oshima, Masaki Kitsunezuka, Kazuaki Kunihiro, NEC, Japan

496  
**Hairpin Bandpass Filter with Tunable Center Frequency and Tunable Bandwidth Based on Screen Printed Ferroelectric Varactors**  
Christian Schuster1, Alex Wiens1, Martin Schüßler1, Christian Kohler2, Joachim R. Binder2, Rolf Jakoby1  
1Technische Universität Darmstadt, Germany; 2KIT, Germany

500  
**An Integrated Tunable Electrical-Balance Filter with >60dB Stopband Attenuation and 1.75–3.7GHz Stopband Tuning Range**  
Barend van Liempd, Benjamin Hershberg, Piet Wambacq, Jan Craninckx, imec, Belgium

504  
**Dual-Mode-Resonator-Based Pseudo-Elliptic Filters with Tunable Response**  
Ahmad Bader Alothman Alterkawi, Fabrizio Gentili, Sebastian W. Sattler, Wolfgang Bösch, Technische Universität Graz, Austria
### EuMIC/EuMC06: Packaged and Integrated High-Power Amplifiers

**Chair:** Peter Aaen, University of Surrey  
**Co-Chair:** Olof Bengtsson, FBH  
**Room:** 14, Time: 14:20–16:00, Tuesday 4th October 2016

<table>
<thead>
<tr>
<th>Page</th>
<th>Title</th>
<th>Authors</th>
</tr>
</thead>
<tbody>
<tr>
<td>508</td>
<td>A Packaged Hybrid Doherty PA for Microwave Links</td>
<td>D. Gustafsson, K. Andersson, A. Leidenhed, M. Malmstrom, A. Rhodin, T. Wegeland, Ericsson, Sweden</td>
</tr>
<tr>
<td>512</td>
<td>A 2.6-GHz-Band 78-W Doherty Power Amplifier with GaN HEMT Unit-Cell Structure Robust for Layout-Dependent Loop Oscillation</td>
<td>Shohei Imai, Shinsuke Watanabe, Yuji Komatsuzaki, Hiroyuki Okazaki, Shintaro Shinjo, Koji Yamanaka, Yoshinobu Sasaki, Hideaki Katayama, Akira Inoue, Mitsubishi Electric, Japan</td>
</tr>
<tr>
<td>516</td>
<td>Linearity Enhancement in CMOS Power Amplifier Design by Using Varactor-Embedded Output Matching Network</td>
<td>Chenxi Zhai, Kwok-Keung M. Cheng, Chinese University of Hong Kong, China</td>
</tr>
<tr>
<td>520</td>
<td>A 20W and Broadband Two-Stage LDMOS Power Amplifier with High-Q Cu Integrated Passive Device for Multi-Band and Multi-Standard Applications</td>
<td>Seungkee Min, Jangheon Kim, Margaret Szymanski, Geoff Tucker, NXP Semiconductors, USA</td>
</tr>
<tr>
<td>524</td>
<td>High Performance Plastic Packaged 100W L-Band Quasi-MMIC HPA</td>
<td>Diane Bouw, Philippe Sin, Marc Camiade, Jean Pierre Viaud, United Monolithic Semiconductors, France</td>
</tr>
</tbody>
</table>

### EuMIC/EuMC07: Packaging and Multichip Modules

**Chair:** Pierre Blondy, XLIM CNRS Universite de Limoges  
**Co-Chair:** Fabio Coccetti, LAAS-CNRS  
**Room:** 15, Time: 14:20–16:00, Tuesday 4th October 2016

<table>
<thead>
<tr>
<th>Page</th>
<th>Title</th>
<th>Authors</th>
</tr>
</thead>
</table>
| 528  | Dielectric Material Characterization of High Frequency Printed Circuit Board Laminates and an Analysis of their Transmission Line High Frequency Losses | Brian Curran¹, Christian Tschohan¹, Ivan Ndip¹, Klaus-Dieter Lang¹, Helmut Kroener², Alexander Iplich²  
¹Fraunhofer IZM, Germany; ²Isola, Germany |
| 532  | Interposer Based on Metallic-nanowire-Membrane (MnM) for mm-Wave Applications | M.V. Pelegrini¹, J.M. Pinheiro¹, L.G. Gomes¹, G.P. Rehder¹, A.L.C. Serrano¹, Florence Podevin², Philippe Ferrari²  
¹Universidade de São Paulo, Brazil; ²IMEP-LAHC, France |
| 536  | Differential Wideband Interconnects for Organic Millimeter Wave Chip Packages: An Effort to Design an All-Purpose RF Chip Package | Franz Xaver Rohrl¹, Johannes Jakob¹, Werner Bogner¹, Daniel Hageneder², Stefan Zorn²  
¹Technische Hochschule Deggendorf, Germany; ²Rohde & Schwarz, Germany |
| 540  | Low-Cost Antenna-in-Package Solution for 122GHz Radar Module         | Akanksha Bhutani¹, Benjamin Goettle¹, Thomas Streitz¹, Steffen Scherr¹, Wolfgang Winkler², Thomas Zwick¹  
¹KIT, Germany; ²Silicon Radar, Germany |
| 544  | 3D Inkjet Printed Radio Frequency Inductors and Capacitors           | Mohammad Vaseem, Garret McKerricher, Atif Shamim, KAUST, Saudi Arabia |
Additional Papers:

548  A 25 to 45 GHz SiGe Receiver MMIC  
     *L. Milner, J. Harvey, M. Parker, L. Hall, M. Rodríguez, M. Heimlich, S. Mahon*

552  150 GHz GaAs Amplifiers in a Commercial 0.1-µm GaAs PHEMT Process  
     *A. Bessemoulin, M. Rodríguez, S. Mahon, A. Parker, M. Heimlich*

556  A New Current Dependent Gate Charge Model for GaN HFET Devices  
     *J. Leckey*